

# Abstracts

## A W-Band, High-Gain, Low-Noise Amplifier Using PHEMT MMIC

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*T.N. Ton, B. Allen, H. Wang, G.S. Dow, E. Barnachea and J. Berenz. "A W-Band, High-Gain, Low-Noise Amplifier Using PHEMT MMIC." 1992 Microwave and Guided Wave Letters 2.2 (Feb. 1992 [MGWL]): 63-64.*

A W-band, high-gain, low-noise amplifier based on pseudomorphic InGaAs/GaAs HEMT devices has been developed. The amplifier has a measured about 50-dB stable gain, and 6-dB noise figure from 91 to 95 GHz. The overall amplifier measured 1.068" x1.281" x0.72" and consumes a total dc power of 560 mW. These results demonstrate the highest gain ever achieved at these frequencies.

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